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| Substitute for form 1449/PTO SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary) | | Complete if Known | | | |
| | | Application Number | 10/684,713 | | |
| | | Filing Date | 10/14/2003 | | |
| | | First Named Inventor | Paul Arthur Layman | | |
| | | Art Unit | 2811 | | |
| | | Examiner Name | Unassigned | | |
| Sheet | 2 | of | 2 | Attorney Docket Number | Chaudhry 25-18-8-12-5/075903-282 |

| NON PATENT LITERATURE DOCUMENTS | | | |
|---------------------------------|-----------------------|---|----------------|
| Examiner Initials* | Cite No. ¹ | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | T ² |
| RP | 1 | DUDEK, ET AL, "Lithography-Independent Nanometer Silicon MOSFET's on Insulator", IEEE Transactions on Electron Devices, Vol. 43, No. 10, October 1996, pp. 1626-1631. | |
| RP | 2 | RISCH, ET AL, "Vertical MOS Transistors with 70 nm Channel Length", IEEE Transactions on Electron Devices, Vol. 43, No. 9, September 1996, pp. 1495-1498. | |
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| RP | 5 | HERGENROTHER, ET AL, "The Vertical Replacement-Gate (VRG) MOSFET: A 50-nm Vertical MOSFET with Lithography-Independent Gate Length", Technical Digest of IEDM, 1999, pp. 75-78. | |
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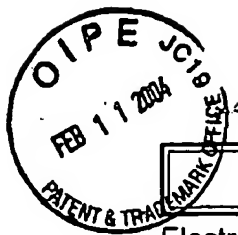
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| Examiner Signature | <i>for Pompey</i> | Date Considered | 6-28-03 |
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

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| Title of Invention | Multiple Operating Voltage Vertical Replacement-Gate (VRG) Transistor | | | | | | |
| <div>Application Number: 10/684713</div> <div>Confirmation Number: 4836</div> <div>First Named Applicant: Paul Layman</div> <div>Attorney Docket Number: 075903-282</div> <div>Art Unit: 2811</div> <div>Search string: (4670768 or 5010386 or 5140388 or 5502009 or 5861347 or 6300199 or 6309930 or 6387758 or 4366495 or 4455565 or 4587713 or 4683643 or 4786953 or 4837606 or 5342797 or 6027975 or 6072216 or 6133099 or 6197641 or 6133164 or 5414289 or 5576238 or 5668391 or 5744846 or 6297531 or 4951102 or 5208172 or 5545586 or 5554870 or 5864158 or 6268621).pn.</div> <div></div> | | | | | | | |
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Signature

| Examiner Name | Date |
|------------------|----------------|
| <i>Rm Pompey</i> | <i>6-28-05</i> |